

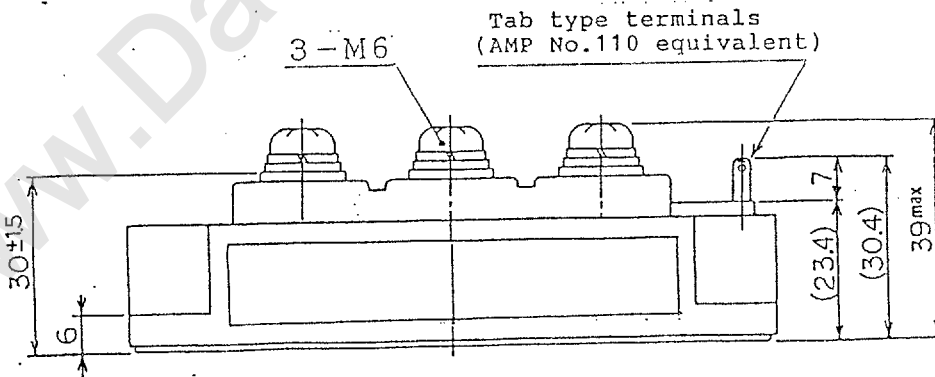
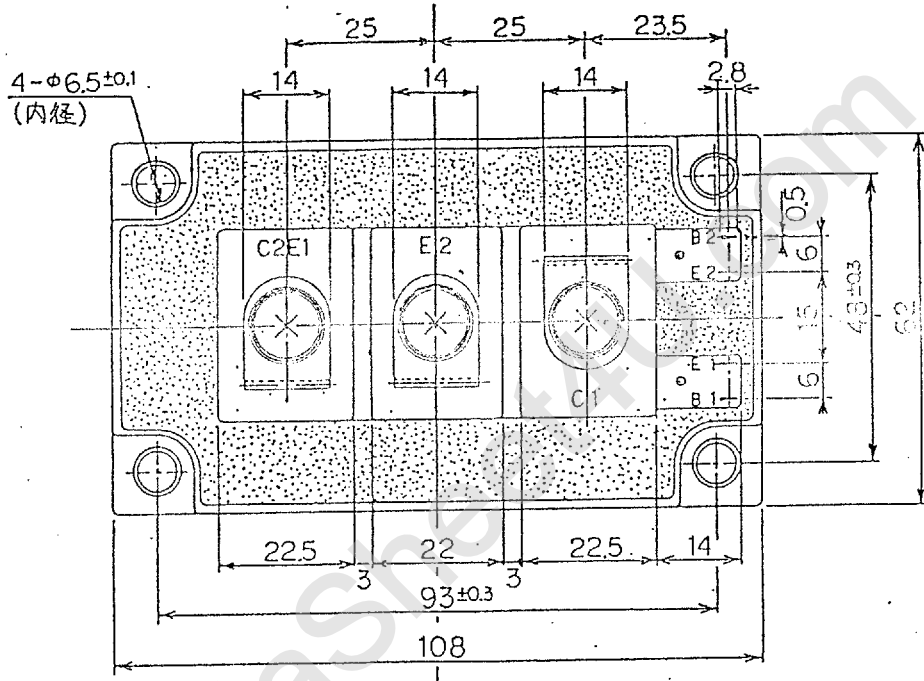
Ratings and characteristics of Fuji IGBT (MBT) Module

2MBI100J-120 (TENTATIVE)

1. Outline Drawing

Unit : mm

* Isolation Voltage : AC 2500 V 1 minute



This material and the information herein is the property of Fuji Electric Co., Ltd. They shall be neither reproduced, copied, lent, or disclosed in any way whatsoever for the use of any third party nor used for the manufacturing purposes without the express written consent of Fuji Electric Co., Ltd.

① Revised page 2-1 and added page 4-11, Apr. 5, '93, A. Yamashita, Z-1

REVISIONS	DATE	NAME	APPROVED
DRAWN	Dec-11-92	N. Iwamoto	
CHECKED	Dec-15-92	T. Miyasaka	

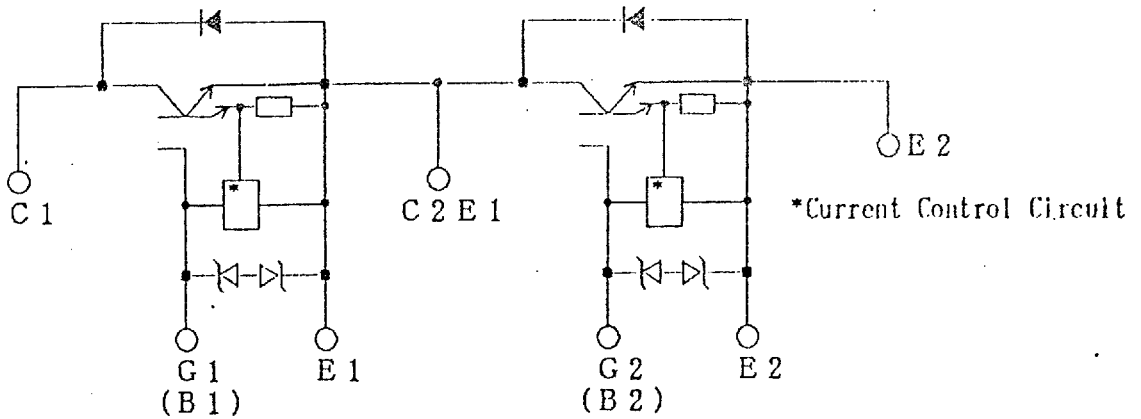
Fuji Electric Co., Ltd.

DWG NO

MT5 F 5032

1/11

2. Equivalent Circuit



3. Absolute Maximum Ratings (Tj=25°C)

Items		Symbols	Ratings	Units
Collector-emitter voltage		V_{CES}	1 2 0 0	V
Gate-emitter voltage		V_{GES}	$\pm 2 0$	V
Collector current	Continuous	I_c	1 0 0	A
	1 ms	I_c pulse	2 0 0	
		$- I_c$	1 0 0	
	1 ms	$- I_c$ pulse	2 0 0	
Max.power dissipation		PC	6 4 0	W
Operating temperature		Tj	+ 1 5 0	°C
Storage temperature		Tstg	- 4 0 ~ + 1 2 5	°C
Isolation voltage		Vis	AC 2 5 0 0 (1min)	V
Screw Torque		Mounting * 1	3. 5	N · m
		Terminals * 2	4. 5	

Note : *1 Recommendable Value : 2.5 ~ 3.5 N · m (M5)
 *2 Recommendable Value : 3.5 ~ 4.5 N · m (M6)

This material and the information herein is the property of
 Fuji Electric Co., Ltd. They shall be neither reproduced, copied,
 lent, or disclosed in any way whatsoever for the use of any
 third party nor used for the manufacturing purposes without
 the express written consent of Fuji Electric Co., Ltd.

REVISIONS			
-----------	--	--	--

	DATE	NAME	APPROVED	Fuji Electric Co., Ltd.	
DRAWN	- -			DWG. NO.	MT5 F 5032
CHECKED	- -				

4. Static electrical characteristics (at Tj=25°C unless otherwise specified)

Items	Symbols	Characteristics			Conditions		Units
		min.	typ.	max.			
Zero gate voltage collector current	I _{CES}			2.0	Tj= 25°C	V _{GE} =0V	mA
					Tj=125°C	V _{CE} =1200V	mA
Gate-emitter leakage current	I _{GES}			30	V _{CE} = 0 V V _{GE} = ±20V		μA
Gate-emitter threshold voltage	V _{GE(LA)}		5.0		V _{CE} =20V I _C = 100mA		V
Collector-emitter saturation voltage	V _{CE(sat)}		2.2		V _{GE} =15V I _C = 100A		V

5. Dynamic ratings (at Tj=25°C unless otherwise specified)

Items	Symbols	Characteristics			Conditions	Units
		min.	typ.	max.		
Input capacitance	C _{ies}		12000		V _{GE} = 0 V	p F
Output capacitance	C _{oes}		-		V _{CE} =10V	
Reverse transfer capacitance	C _{res}		-		f = 1 MHz	
Turn-on time	t _{on}		0.8		V _{CC} =600V I _C = 100A V _{GE} = ±15V R _G = 9.1Ω	μ s
	t _r		0.3			
Turn-off time	t _{off}		1.0			
	t _f		0.2			

This material and the information herein is the property of Fuji Electric Co., Ltd. They shall be neither reproduced, copied, lent, or disclosed in any way whatsoever for the use of any third party, nor used for the manufacturing purposes without the express written consent of Fuji Electric Co., Ltd.

	DATE	NAME	APPROVED	Fuji Electric Co., Ltd.	
DRAWN	- -			DWG. NO.	MT5 F 5032
CHECKED	- -				
REVISIONS					

